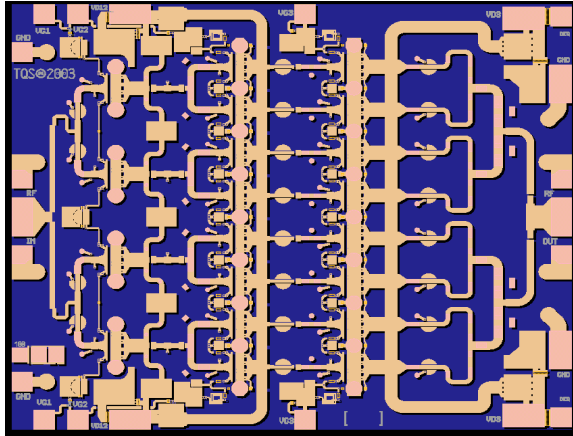


## Ka Band 2W Power Amplifier



### Key Features

- 30 - 40 GHz Bandwidth
- > 33 dBm Nominal Psat @ Pin = 20dBm
- 18 dB Nominal Gain
- Bias: 6 V, 1050 mA Idq (1.9A under RF Drive)
- 0.15 um 3MI pHEMT Technology
- Chip Dimensions: 2.79 x 2.315 x 0.1 mm (0.110 x 0.091 x 0.004) in

### Primary Applications

- Military Radar Systems
- Ka-Band Sat-Com
- Point to Point Radio

### Product Description

The TriQuint TGA4516 is a High Power MMIC Amplifier for Ka-band applications. The part is designed using TriQuint's 0.15um power pHEMT process. The small chip size is achieved by utilizing TriQuint's 3 metal layer interconnect (3MI) design technology that allows compaction of the design over competing products.

The TGA4516 provides >33 dBm saturated output power, and has typical gain of 18 dB at a bias of 6V and 1050mA (Idq). The current rises to 1.9A under RF drive.

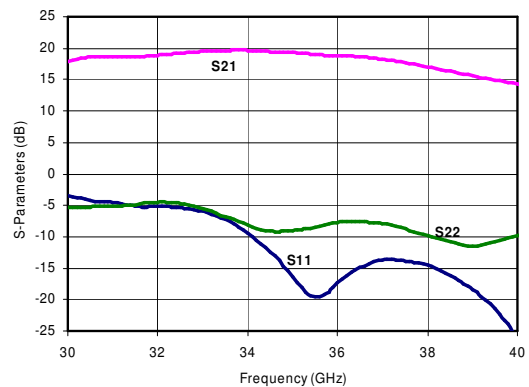
This HPA is ideally suited for many applications such as Military Radar Systems, Ka-band Sat-Com, and Point-to-Point Radios.

The TGA4516 is 100% DC and RF tested on-wafer to ensure performance compliance.

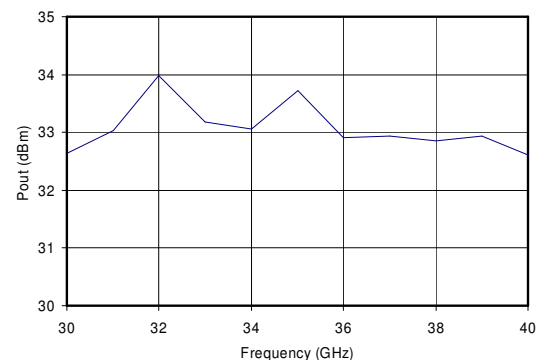
Lead-Free & RoHS compliant.

### Fixtured Data

$V_D = 6V, I_D = 1050mA$



Pout @ Pin = 20dBm



**TABLE I**  
**MAXIMUM RATINGS 1/**

SYMBOL	PARAMETER	VALUE	NOTES
V <sup>+</sup>	Positive Supply Voltage	6.5 V	<u>2/</u>
V <sup>-</sup>	Negative Supply Voltage Range	-5 TO 0 V	
I <sup>+</sup>	Positive Supply Current	3 A	<u>2/ 3/</u>
I <sub>G</sub>	Gate Supply Current	85 mA	<u>3/</u>
P <sub>IN</sub>	Input Continuous Wave Power	267 mW	
P <sub>D</sub>	Power Dissipation	12.7 W	<u>2/ 4/</u>
T <sub>CH</sub>	Operating Channel Temperature	200 °C	<u>5/ 6/</u>
	Mounting Temperature (30 Seconds)	320 °C	
T <sub>STG</sub>	Storage Temperature	-65 to 150 °C	

- 1/ These ratings represent the maximum operable values for this device.
- 2/ Combinations of supply voltage, supply current, input power, and output power shall not exceed P<sub>D</sub>.
- 3/ Total current for the entire MMIC.
- 4/ When operated at this bias condition with a base plate temperature of 70 °C, the median life is 7.3E3 hrs.
- 5/ Junction operating temperature will directly affect the device median time to failure (T<sub>m</sub>). For maximum life, it is recommended that junction temperatures be maintained at the lowest possible levels.
- 6/ These ratings apply to each individual FET.

**TABLE II**  
**ELECTRICAL CHARACTERISTICS**  
(Ta = 25 °C, Nominal)

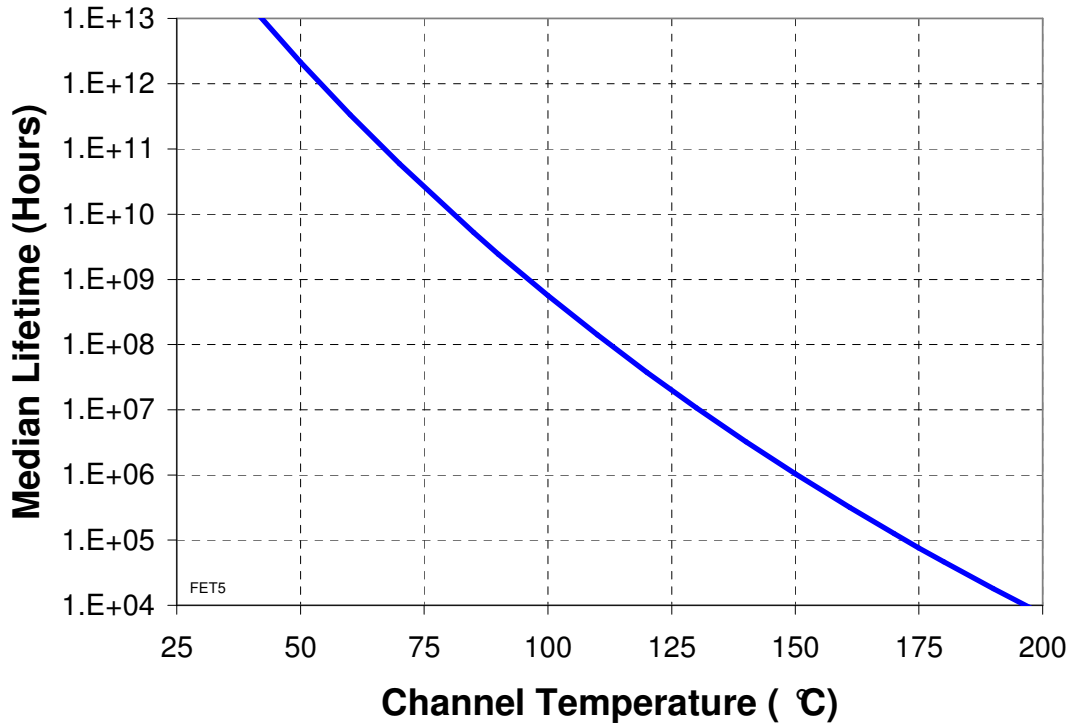
PARAMETER	TYPICAL	UNITS
Drain Operating	6	V
Quiescent Current	1050	mA
Frequency Range	30 - 40	GHz
Small Signal Gain, S21	18	dB
Input Return Loss, S11	10	dB
Output Return Loss, S22	7	dB
Power @ saturated, Psat	33	dBm

**TABLE III  
THERMAL INFORMATION**

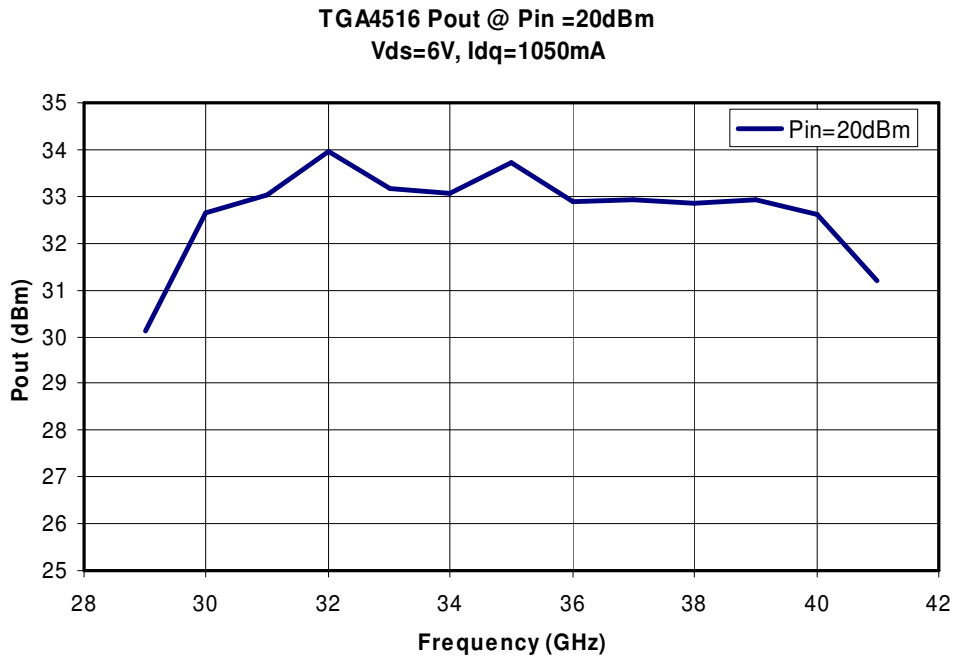
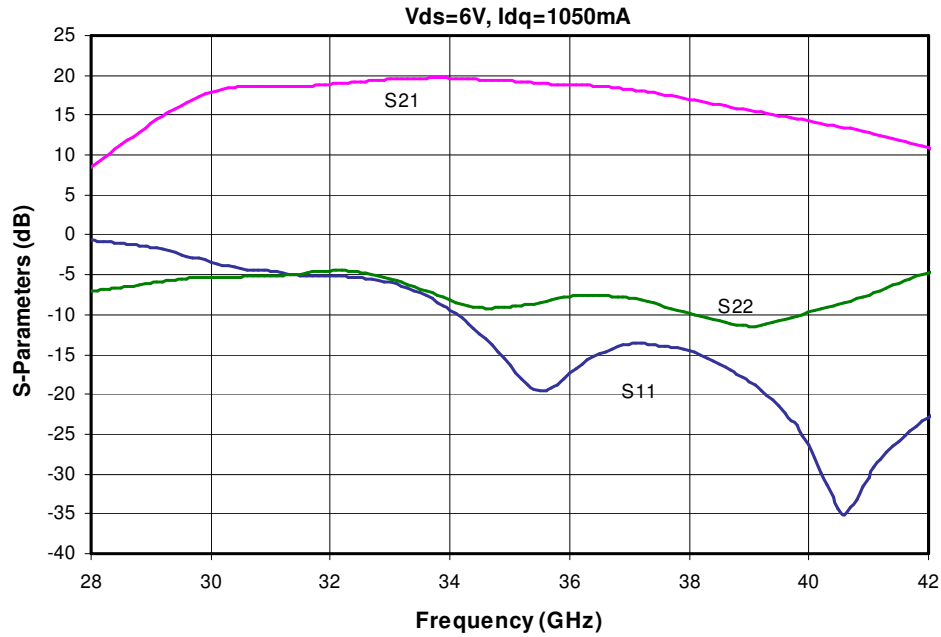
Parameter	Test Conditions	T <sub>ch</sub> (°C)	θ <sub>JC</sub> (°C/W)	T <sub>m</sub> (HRS)
<b>θ<sub>JC</sub> Thermal Resistance</b> (channel to backside of carrier)	Vd = 6 V Id = 1700 mA Freq = 35 GHz Pdiss = 7.8 W	150	10.2	1E+6

Note: Assumes eutectic attach using 1.5 mil 80/20 AuSn mounted to a 20 mil CuMo Carrier at 70°C baseplate temperature. Worst case is at saturated output power when DC power consumption rises to 10.6 W with 2.3 W RF power delivered to load. Power dissipated is 8.2 W and the temperature rise in the channel is 84 °C.

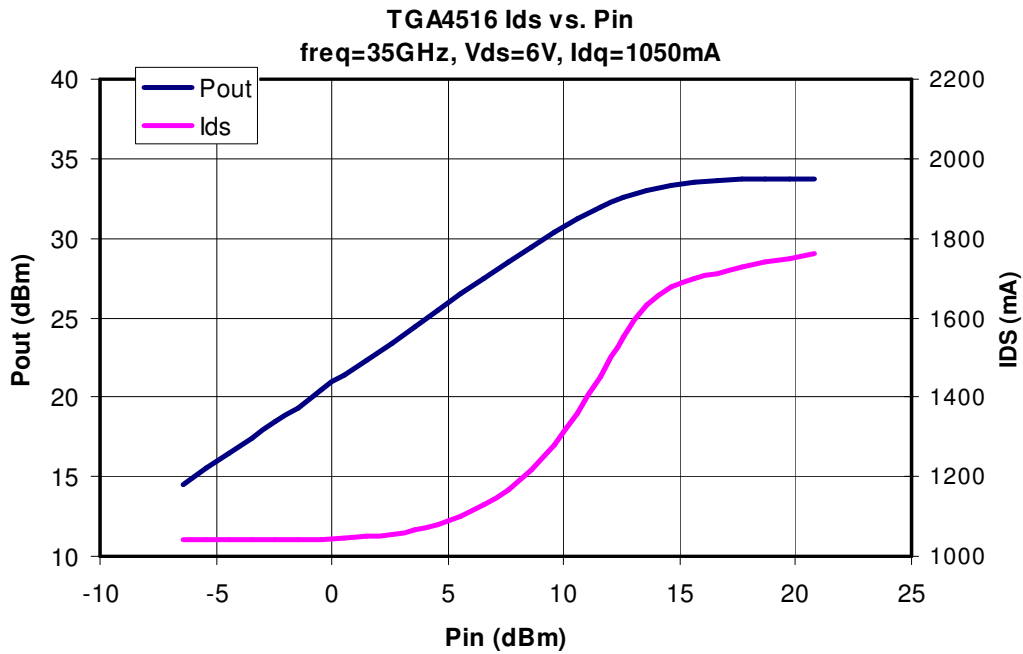
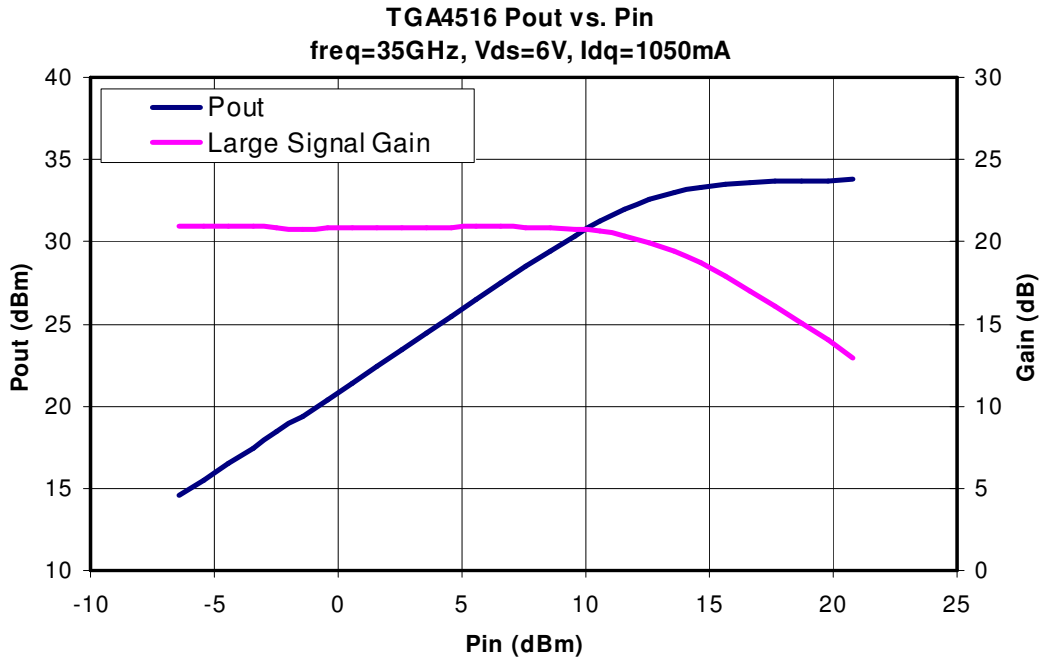
**Median Lifetime (T<sub>m</sub>) vs. Channel Temperature**



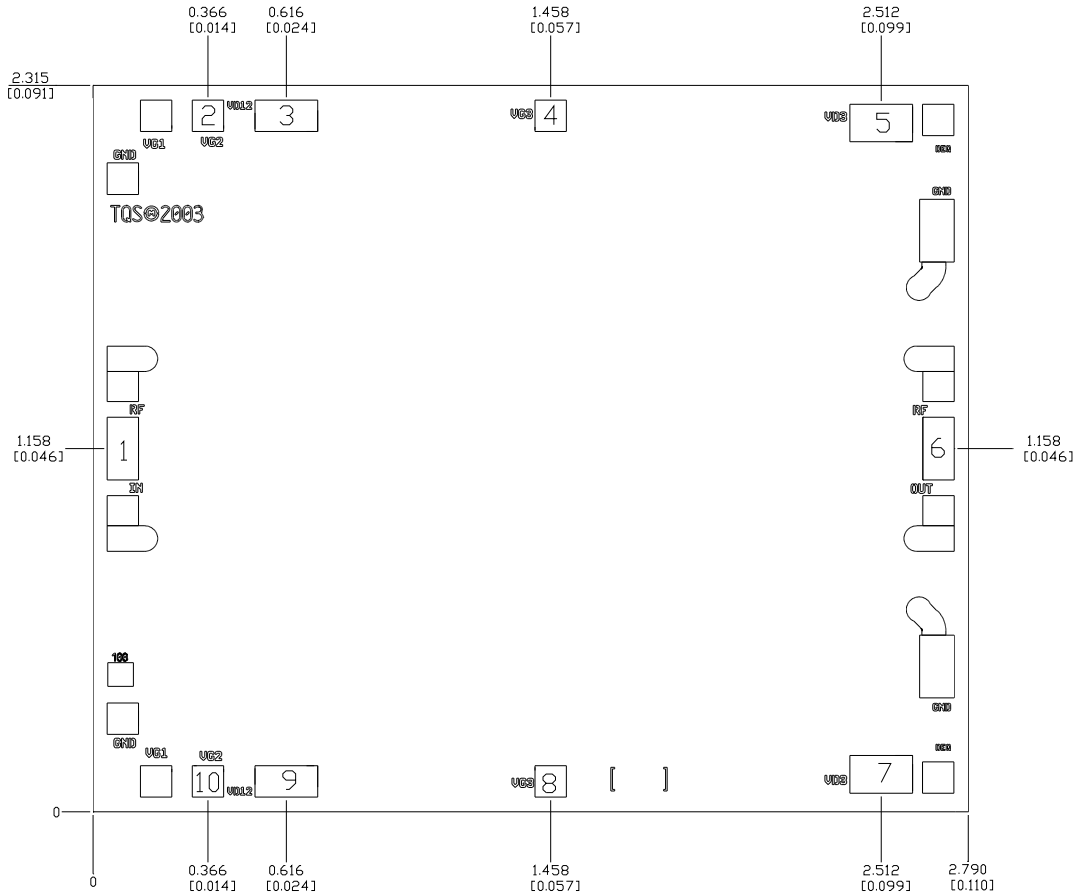
**Fixture Performance**



### Fixture Performance



**Mechanical Drawing**



**Units: Millimeters [inches]**

**Thickness: 0.100 [0.004] (reference only)**

**Chip edge to bond pad dimensions are shown to center of bond pad**

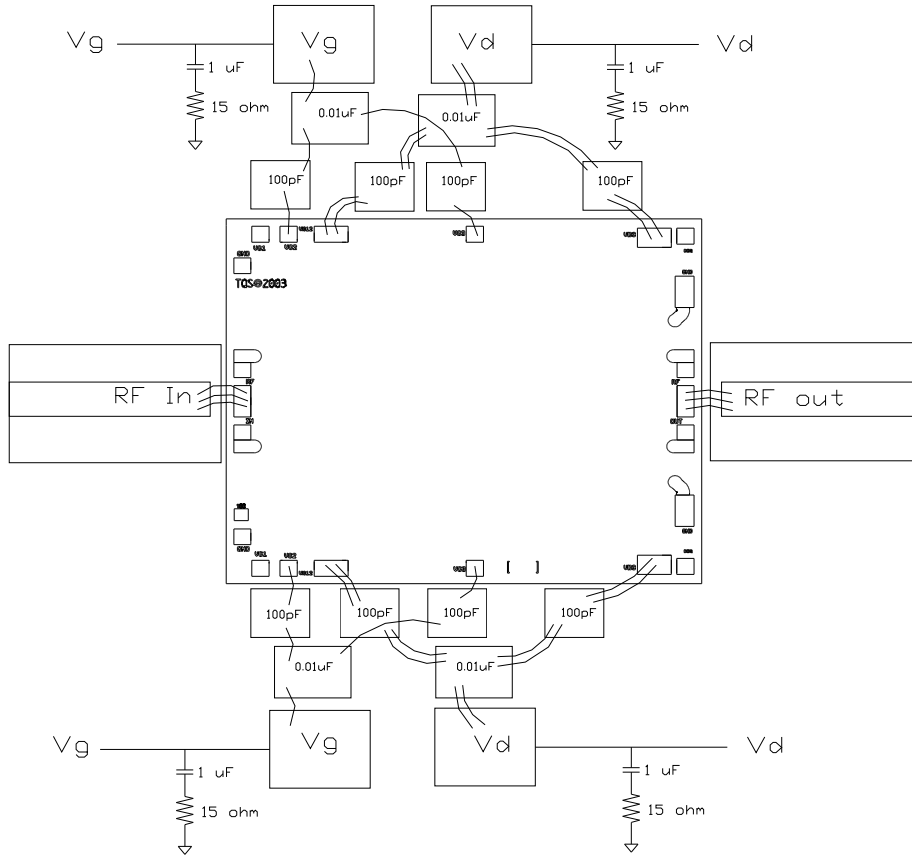
**Chipsize: 2.79 x 2.315 [0.110 x 0.091] +/- 0.51 [0.002]**

**RF Ground is backside of MMIC**

Bond pad #1	(RF Input)	0.100 x 0.200 [0.004 x 0.008]
Bond pad #2	(Vg2)	0.100 x 0.100 [0.004 x 0.004]
Bond pad #3	(Vd12)	0.100 x 0.200 [0.004 x 0.008]
Bond pad #4	(Vg3)	0.100 x 0.100 [0.004 x 0.004]
Bond pad #5	(Vd3)	0.100 x 0.100 [0.004 x 0.004]
Bond pad #6	(RF Output)	0.100 x 0.200 [0.004 x 0.008]
Bond pad #7	(Vd3)	0.100 x 0.200 [0.004 x 0.008]
Bond pad #8	(Vg3)	0.100 x 0.100 [0.004 x 0.004]
Bond pad #9	(Vd12)	0.100 x 0.200 [0.004 x 0.008]
Bond pad #10	(Vg2)	0.100 x 0.100 [0.004 x 0.004]

**GaAs MMIC devices are susceptible to damage from Electrostatic Discharge. Proper precautions should be observed during handling, assembly and test.**

**Chip Assembly Diagram**



**GaAs MMIC devices are susceptible to damage from Electrostatic Discharge. Proper precautions should be observed during handling, assembly and test.**



## **Assembly Process Notes**

### Reflow process assembly notes:

- Use AuSn (80/20) solder with limited exposure to temperatures at or above 300°C (30 seconds max).
- An alloy station or conveyor furnace with reducing atmosphere should be used.
- No fluxes should be utilized.
- Coefficient of thermal expansion matching is critical for long-term reliability.
- Devices must be stored in a dry nitrogen atmosphere.

### Component placement and adhesive attachment assembly notes:

- Vacuum pencils and/or vacuum collets are the preferred method of pick up.
- Air bridges must be avoided during placement.
- The force impact is critical during auto placement.
- Organic attachment can be used in low-power applications.
- Curing should be done in a convection oven; proper exhaust is a safety concern.
- Microwave or radiant curing should not be used because of differential heating.
- Coefficient of thermal expansion matching is critical.

### Interconnect process assembly notes:

- Thermosonic ball bonding is the preferred interconnect technique.
- Force, time, and ultrasonics are critical parameters.
- Aluminum wire should not be used.
- Maximum stage temperature is 200°C.

***GaAs MMIC devices are susceptible to damage from Electrostatic Discharge. Proper precautions should be observed during handling, assembly and test.***